

## EAST Search History

| Ref # | Hits  | Search Query  | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|-------|---|---|------------------|---------|------------------|
| L1    | 44673 | semiconductor and ((thin adj film adj transistor) or tft)   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/08/04 16:28 |
| L2    | 1266  | 1 and ((aluminum adj nitride) or aln)   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/08/04 16:28 |
| L3    | 1253  | 2 and (oxygen or o or carbon or c or (silicon adj (oxide or dioxide)) or sio or (silicon adj carbide) or sic) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/08/04 16:29 |

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|-------|-------|---|---|------------------|---------|------------------|
| L1    | 44673 | semiconductor and ((thin adj film adj transistor) or tft) | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/08/04 17:31 |
| L2    | 21519 | 1 and channel   | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/08/04 17:31 |
| L3    | 2110  | 2 and (laser adj irradiation)                             | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/08/04 17:32 |
| L4    | 1747  | 3 and (silicon adj (oxide or dioxide))                    | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/08/04 17:32 |
| L5    | 1738  | 4 and crystal\$5  | US-PGPUB;<br>USPAT;<br>USOCR;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2006/08/04 17:33 |